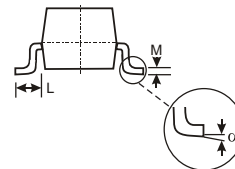
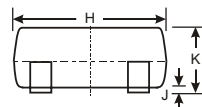
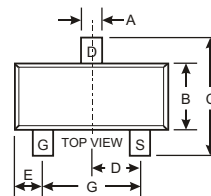


Features

- Super high density cell design for extremely low $R_{DS(ON)}$.
- Fully characterized avalanche voltage and current.
- Excellent package for good heat dissipation.
- We declare that the material of product compliance with RoHS requirements.



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

APPLICATIONS

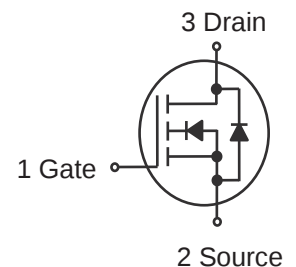
- Power Switching application.
- Hard switchen and high frequency circuits.
- Uninterruptible power supply.
- Marking Code:0102.

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	3.0	A
Peak Drain Current ¹⁾	I_{DM}	20	A
Power Dissipation	P_{tot}	1.5	W
Thermal Resistance from Junction to Ambient (PCB mounted) ²⁾	$R_{\theta JA}$	100	$^\circ\text{C/W}$
Junction Temperature	T_J	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 175	$^\circ\text{C}$

¹⁾ Repetitive Rating: Pulse width limited by the Maximum junction temperature.

²⁾ 1 in² 2oz Cu PCB board.



N-CHANNEL ENHANCEMENT MODE POWER MOSFET

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

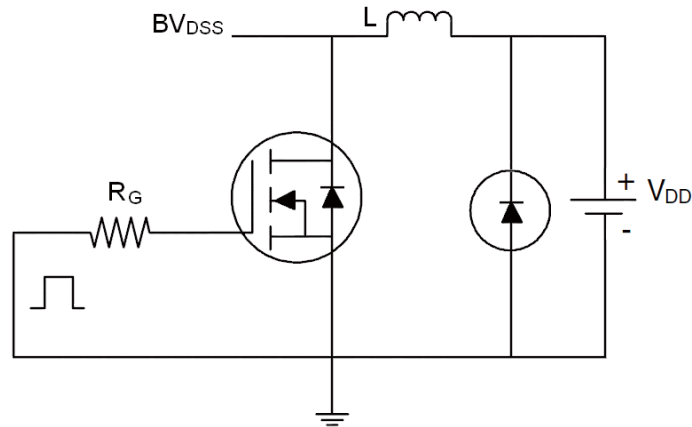
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V		-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V		-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3A	-	136	160	mΩ
		V _{GS} =4.5V, I _D =3A	-	140	170	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =2A	-	5	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	650	-	PF
Output Capacitance	C _{OSS}		-	24	-	PF
Reverse Transfer Capacitance	C _{rSS}		-	20	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, R _L =19Ω V _{GS} =10V, R _G =3Ω	-	6	-	nS
Turn-on Rise Time	t _r		-	4	-	nS
Turn-Off Delay Time	t _{d(off)}		-	20	-	nS
Turn-Off Fall Time	t _f		-	4	-	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =3A, V _{GS} =10V	-	20	-	nC
Gate-Source Charge	Q _{gs}		-	2.1	-	nC
Gate-Drain Charge	Q _{gd}		-	3.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =3A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	3	A

Notes:

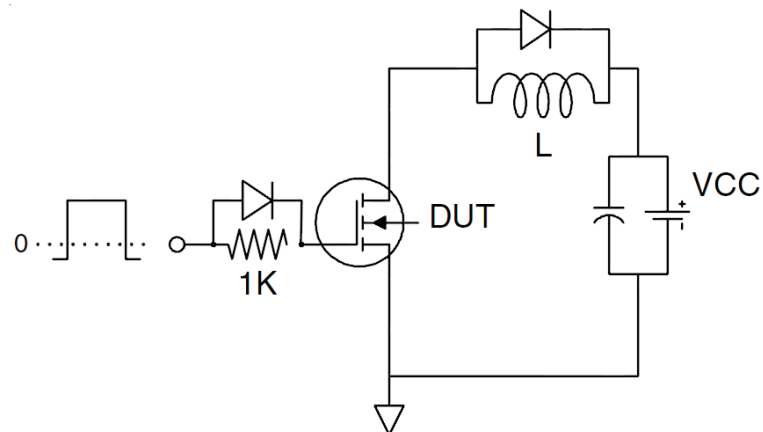
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

TEST CIRCUIT

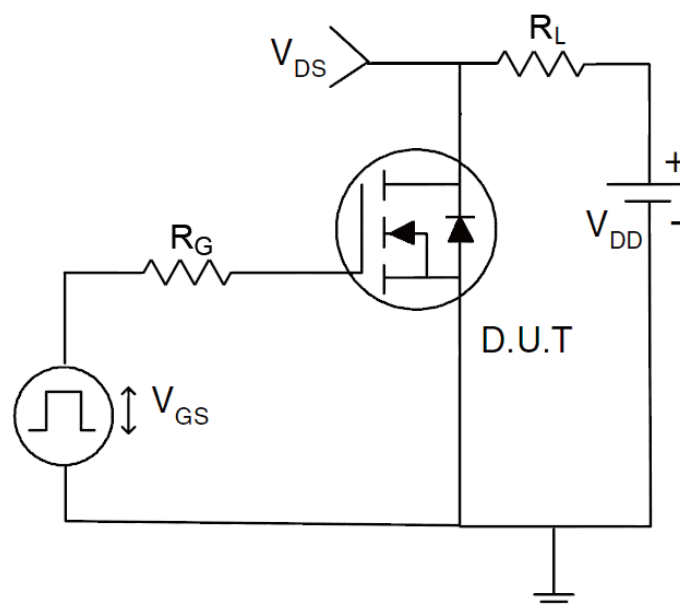
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit



TYPICAL TRANSIENT CHARACTERISTICS

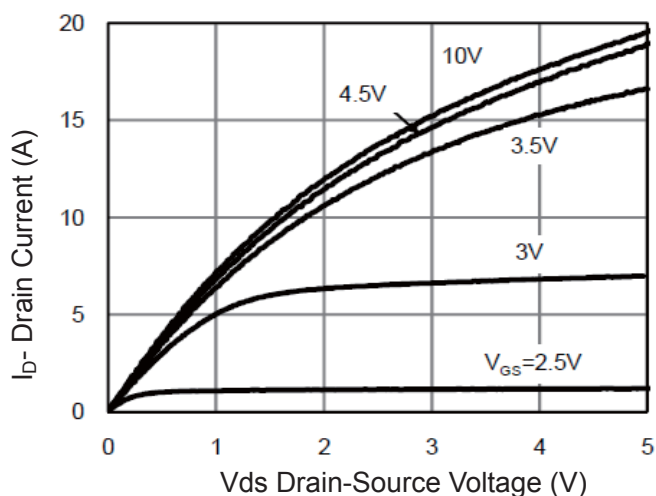


Figure 1 Output Characteristics

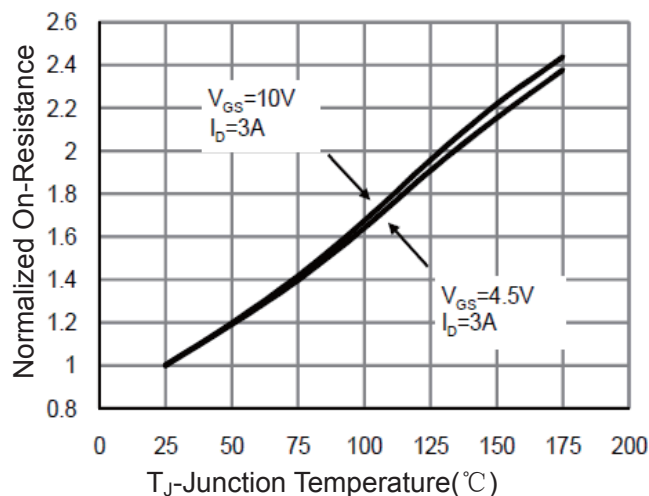


Figure 4 Rdson-Junction Temperature

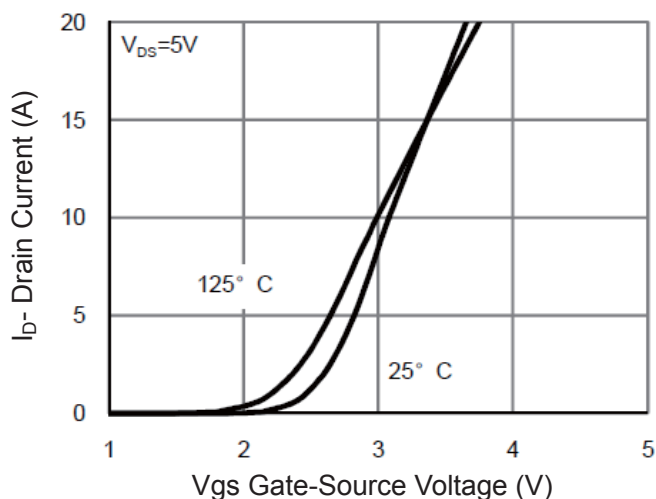


Figure 2 Transfer Characteristics

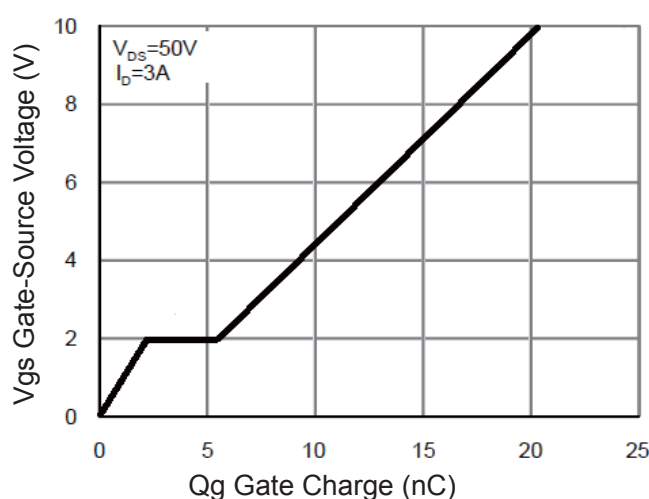


Figure 5 Gate Charge

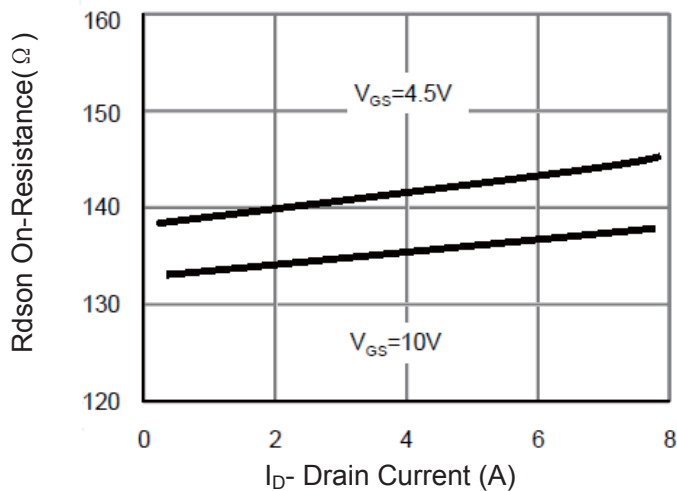


Figure 3 Rdson- Drain Current

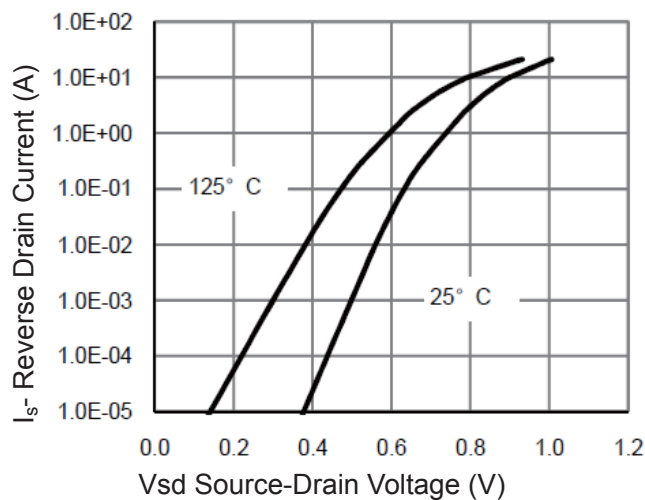


Figure 6 Source- Drain Diode Forward

TYPICAL TRANSIENT CHARACTERISTICS

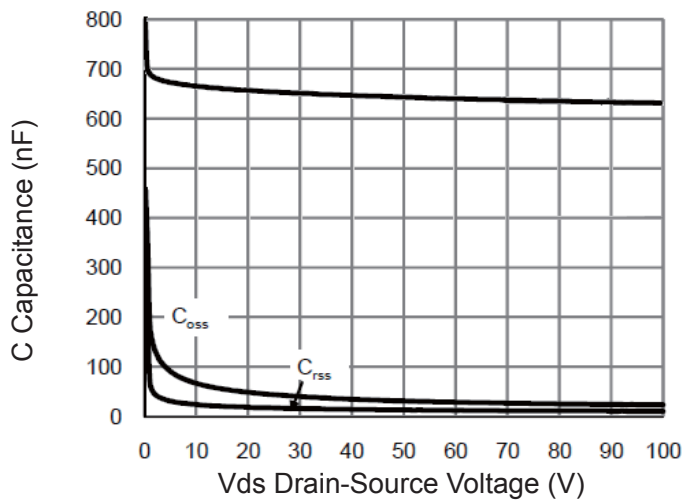


Figure 7 Capacitance vs Vds

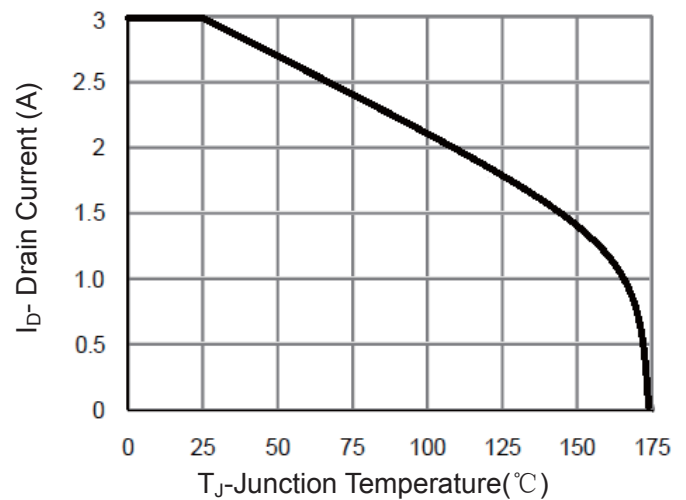


Figure 9 BV_{DSS} vs Junction Temperature

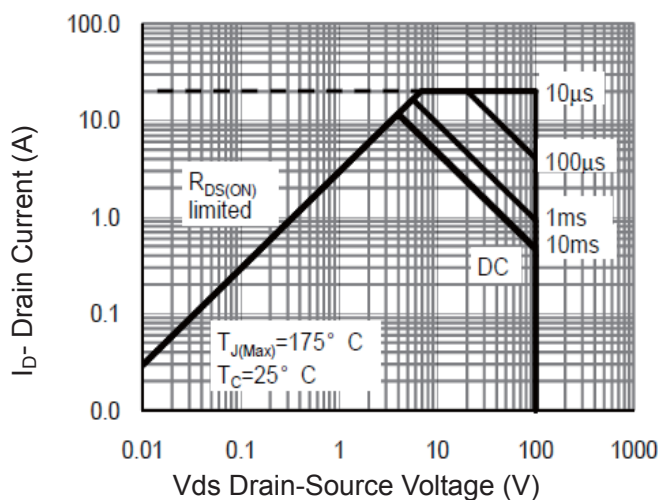


Figure 8 Safe Operation Area

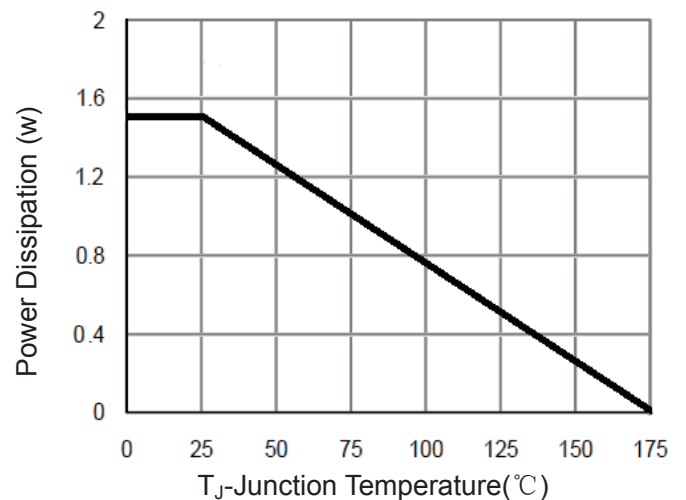


Figure 10 Power De-rating

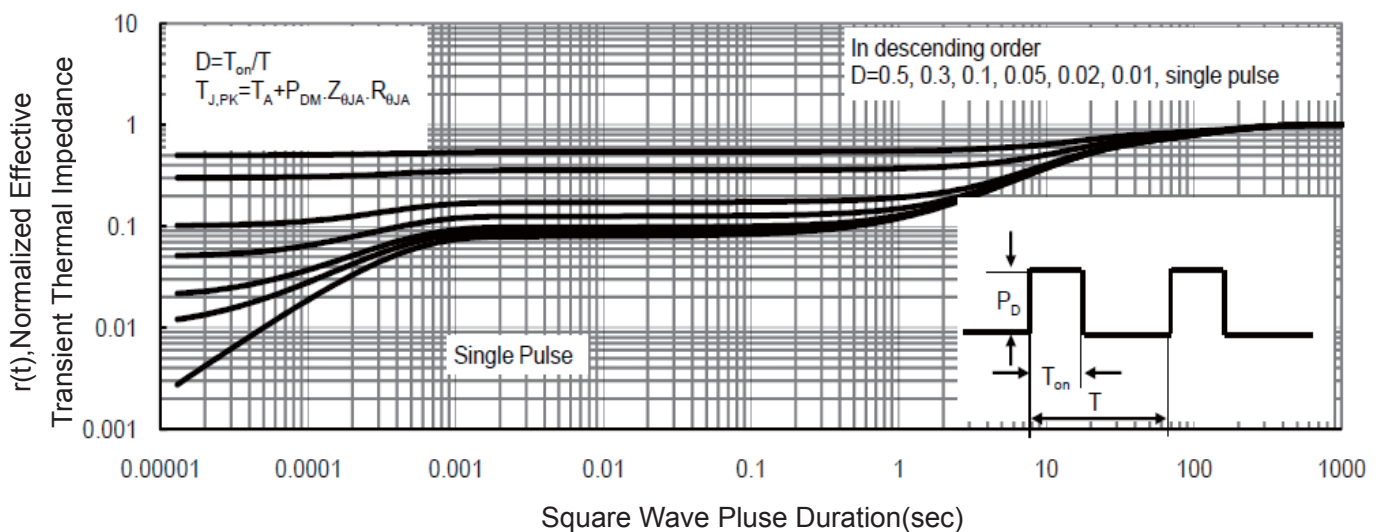


Figure 11 Normalized Maximum Transient Thermal Impedance

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